

FEATURES:

- **Organized as 128K x8 / 256K x8 / 512K x8**
- **2.7-3.6V Read Operation**
- **Superior Reliability**
 - Endurance: At least 1000 Cycles
 - Greater than 100 years Data Retention
- **Low Power Consumption:**
 - Active Current: 10 mA (typical)
 - Standby Current: 2 μ A (typical)
- **Fast Read Access Time:**
 - 70 ns
- **Latched Address and Data**
- **Fast Byte-Program Operation:**
 - Byte-Program Time: 15 μ s (typical)
 - Chip Program Time:
 - 2 seconds (typical) for GLS37VF010
 - 4 seconds (typical) for GLS37VF020
 - 8 seconds (typical) for GLS37VF040
- **Electrical Erase Using Programmer**
 - Does not require UV source
 - Chip-Erase Time: 100 ms (typical)
- **CMOS I/O Compatibility**
- **JEDEC Standard Byte-wide Flash EEPROM Pinouts**
- **Packages Available**
 - 32-lead PLCC
 - 32-lead TSOP (8mm x 14mm)
 - 32-pin PDIP
 - Non-Pb (lead-free) packages available

PRODUCT DESCRIPTION

The GLS37VF010/020/040 devices are 128K x8 / 256K x8 / 512K x8 CMOS, Many-Time Programmable (MTP), low cost flash, manufactured with high performance Super-Flash technology. The split-gate cell design and thick-oxide tunneling injector attain better reliability and manufacturability compared with alternate approaches. The GLS37VF010/020/040 can be electrically erased and programmed at least 1000 times using an external programmer, e.g., to change the contents of devices in inventory. The GLS37VF010/020/040 have to be erased prior to programming. These devices conform to JEDEC standard pinouts for byte-wide flash memories.

Featuring high performance Byte-Program, the GLS37VF010/020/040 provide a typical Byte-Program time of 15 μ s. Designed, manufactured, and tested for a wide spectrum of applications, these devices are offered with an endurance of at least 1000 cycles. Data retention is rated at greater than 100 years.

The GLS37VF010/020/040 are suited for applications that require infrequent writes and low power nonvolatile storage. These devices will improve flexibility, efficiency, and performance while matching the low cost in nonvolatile applications that currently use UV-EPROMs, OTPs, and mask ROMs.

To meet surface mount and conventional through hole requirements, the GLS37VF010/020/040 are offered in 32-lead PLCC, 32-lead TSOP, and 32-pin PDIP packages. See Figures 2, 3, and 4 for pin assignments.

Device Operation

The GLS37VF010/020/040 devices are nonvolatile memory solutions that can be used instead of standard flash devices if in-system programmability is not required. It is functionally (Read) and pin compatible with industry standard flash products. The device supports electrical Erase operation via an external programmer.

Read

The Read operation of the GLS37VF010/020/040 is controlled by CE# and OE#. Both CE# and OE# have to be low for the system to obtain data from the outputs. Once the address is stable, the address access time is equal to the delay from CE# to output (T_{CE}). Data is available at the output after a delay of TOE from the falling edge of OE#, assuming the CE# pin has been low and the addresses have been stable for at least $T_{CE}-T_{OE}$. When the CE# pin is high, the chip is deselected and a standby current of only 2 μ A (typical) is consumed. OE# is the output control and is

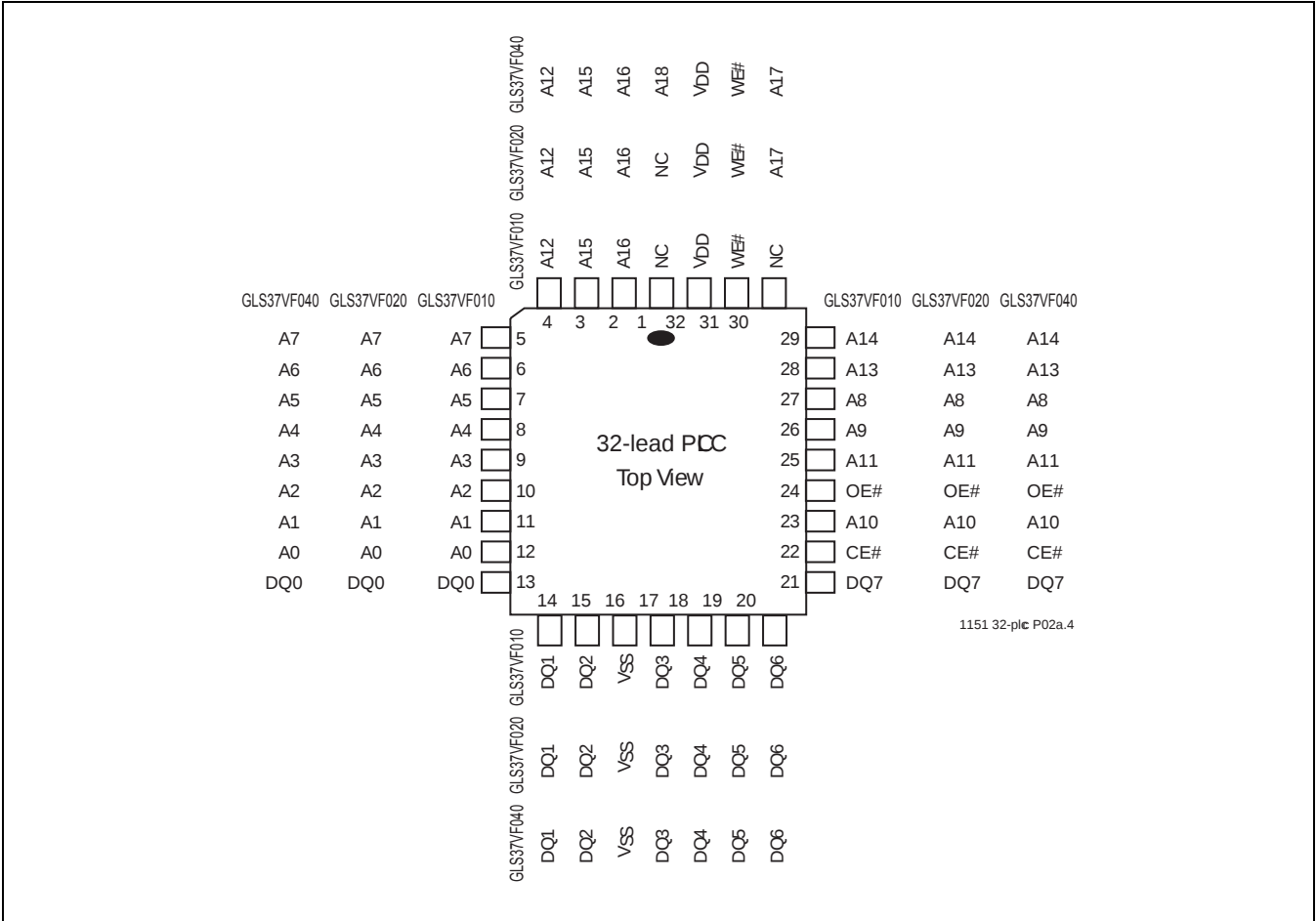


FIGURE 2: Pin Assignments for 32-lead PLCC

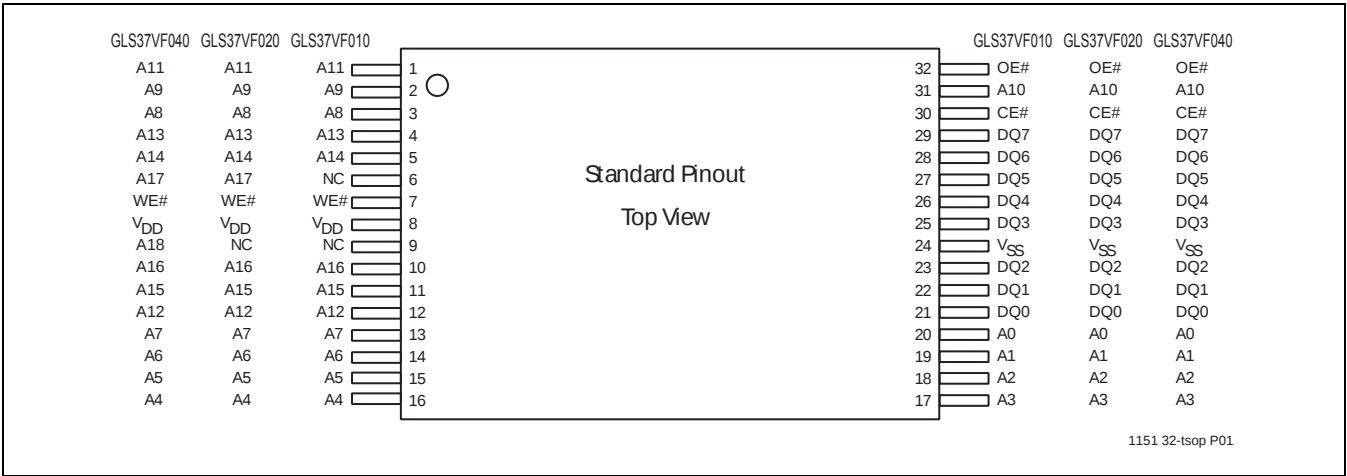


FIGURE 3: Pin Assignments for 32-lead TSOP (8mm x 14mm)



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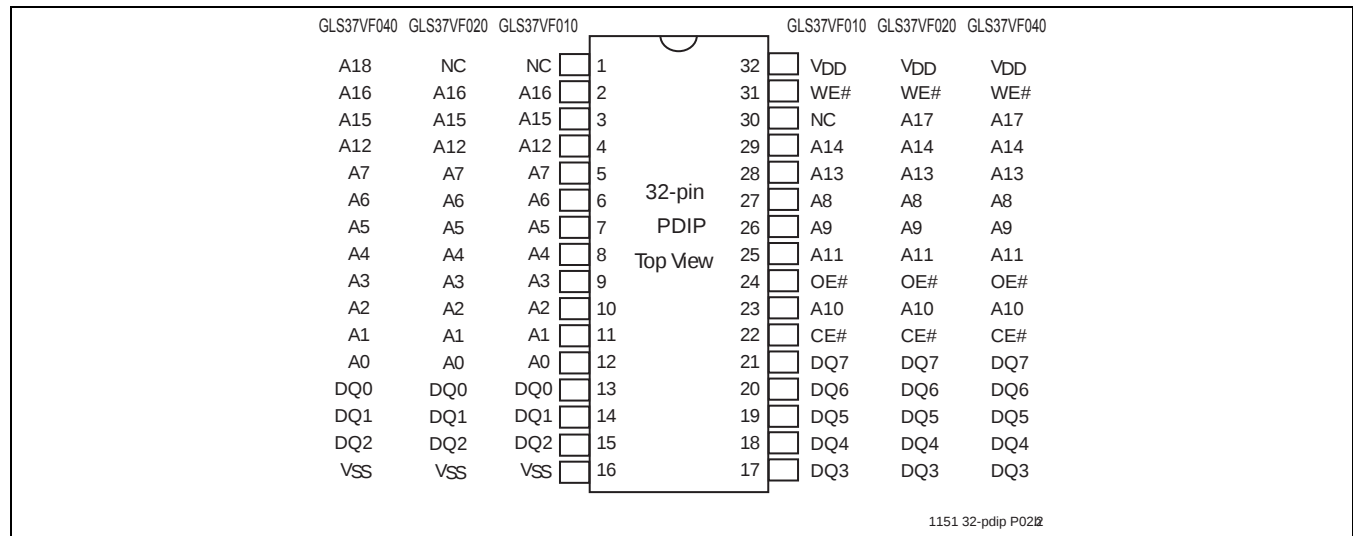


FIGURE 4: Pin Assignments for 32-pin PDIP

TABLE 2: Pin Description

Symbol	Pin Name	Functions
$A_{MS}^1-A_0$	Address Inputs	To provide memory addresses.
DQ_7-DQ_0	Data Input/output	To output data during Read cycles and receive input data during Program cycles. The outputs are in tri-state when OE# or CE# is high.
CE#	Chip Enable	To activate the device when CE# is low.
WE#	Write Enable	To program or erase (WE# = V_{IL} pulse during Program or Erase)
OE#	Output Enable	To gate the data output buffers during Read operation when low
V_{DD}	Power Supply	To provide 3.0V supply (2.7-3.6V)
V_{SS}	Ground	
NC	No Connection	Unconnected pins.

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1. A_{MS} = Most significant address

A_{MS} = A_{16} for GLS37VF010, A_{17} for GLS37VF020, and A_{18} for GLS37VF040

TABLE 3: Operation Modes Selection

Mode	CE#	WE#	A_9	OE#	DQ	Address
Read	V_{IL}	V_{IH}	A_{IN}	V_{IL}	D_{OUT}	A_{IN}
Output Disable	V_{IL}	X	X	V_{IH}	High Z	A_{IN}
Standby	V_{IH}	X	X	X	High Z	X
Chip-Erase	V_{IL}	V_{IL}	V_H	V_H	High Z	X
Byte-Program	V_{IL}	V_{IL}	A_{IN}	V_H	D_{IN}	A_{IN}
Program/Erase Inhibit	X	V_{IH}	X	X	High Z	X
	X	X	X	V_{IL} or V_{IH}	High Z/ D_{OUT}	X
Product Identification	V_{IL}	V_{IH}	V_H	V_{IL}	Manufacturer's ID (BFH) Device ID ¹	$A_{MS}^2 - A_1 = V_{IL}$, $A_0 = V_{IL}$ $A_{MS}^2 - A_1 = V_{IL}$, $A_0 = V_{IH}$

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1. Device ID = C5H for GLS37VF020, C6H for GLS37VF020, and C2H for GLS37VF040

2. A_{MS} = Most significant address

A_{MS} = A_{16} for GLS37VF010, A_{17} for GLS37VF020, and A_{18} for GLS37VF040

Note: X = V_{IL} or V_{IH} (or V_H in case of OE# and A_9)

V_H = 11.4-12V

Absolute Maximum Stress Ratings (Applied conditions greater than those listed under “Absolute Maximum Stress Ratings” may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these conditions or conditions greater than those defined in the operational sections of this data sheet is not implied. Exposure to absolute maximum stress rating conditions may affect device reliability.)

Temperature Under Bias -55°C to +125°C
 Storage Temperature -65°C to +150°C
 D. C. Voltage on Any Pin to Ground Potential -0.5V to $V_{DD}+0.5V$
 Transient Voltage (<20 ns) on Any Pin to Ground Potential -2.0V to $V_{DD}+2.0V$
 Voltage on A_9 Pin to Ground Potential -0.5V to 13.2V
 Package Power Dissipation Capability ($T_A = 25^\circ C$) 1.0W
 Through Hole Lead Soldering Temperature (10 Seconds) 300°C
 Surface Mount Solder Reflow Temperature: “with-Pb” units¹: 240°C for 3 seconds
 “non-Pb” units: 260°C for 3 seconds
 Output Short Circuit Current² 50 mA

1. Certain “with-Pb” package types are capable of 260°C for 3 seconds; please consult the factory for the latest information.
2. Outputs shorted for no more than one second. No more than one output shorted at a time.

OPERATING RANGE

Range	Ambient Temp	V_{DD}
Commercial	0°C to +70°C	2.7-3.6V

AC CONDITIONS OF TEST

Input Rise/Fall Time	5 ns
Output Load	$C_L = 100$ pF
See Figures 8 and 9	

TABLE 4: Read Mode DC Operating Characteristics $V_{DD}=2.7-3.6V$ ($T_A = 0^\circ C$ to +70°C (Commercial))

Symbol	Parameter	Limits			Test Conditions
		Min	Max	Units	
I_{DD}	V_{DD} Read Current		12	mA	Address input= V_{ILT}/V_{IHT} , at $f=1/T_{RC}$ Min $V_{DD}=V_{DD}$ Max $CE\#=V_{IL}$, $OE\#=V_{IHT}$, all I/Os open
I_{SB}	Standby V_{DD} Current		15	μA	$CE\#=V_{IHC}$, $V_{DD}=V_{DD}$ Max
I_{LI}	Input Leakage Current		1	μA	$V_{IN}=GND$ to V_{DD} , $V_{DD}=V_{DD}$ Max
I_{LO}	Output Leakage Current		10	μA	$V_{OUT}=GND$ to V_{DD} , $V_{DD}=V_{DD}$ Max
V_{IL}	Input Low Voltage		0.8	V	$V_{DD}=V_{DD}$ Min
V_{IH}	Input High Voltage	0.7 V_{DD}		V	$V_{DD}=V_{DD}$ Max
V_{IHC}	Input High Voltage (CMOS)	$V_{DD}-0.3$		V	$V_{DD}=V_{DD}$ Max
V_{OL}	Output Low Voltage		0.2	V	$I_{OL}=100$ μA , $V_{DD}=V_{DD}$ Min
V_{OH}	Output High Voltage	$V_{DD}-0.3$		V	$I_{OH}=-100$ μA , $V_{DD}=V_{DD}$ Min
I_H	Supervoltage Current for A_9		200	μA	$CE\#=OE\#=V_{IL}$, $A_9=V_H$ Max

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TABLE 5: Program/Erase DC Operating Characteristics $V_{DD}=2.7-3.6V$ ($T_A = 25^\circ C \pm 5^\circ C$)

Symbol	Parameter	Limits			Test Conditions
		Min	Max	Units	
I_{DD}	V_{DD} Erase or Program Current		20	mA	$CE\#=V_{IL}$, $OE\#=V_H$, $V_{DD}=V_{DD} \text{ Max}$, $WE\#=V_{IL}$
I_{LI}	Input Leakage Current		1	μA	$V_{IN}=GND$ to V_{DD} , $V_{DD}=V_{DD} \text{ Max}$
I_{LO}	Output Leakage Current		10	μA	$V_{OUT}=GND$ to V_{DD} , $V_{DD}=V_{DD} \text{ Max}$
V_H	Supervoltage for A_9 and $OE\#$	11.4	12	V	$OE\#=V_H \text{ Max}$, $A_9=V_H \text{ Max}$, $V_{DD}=V_{DD} \text{ Max}$, $CE\#=V_{IL}$ $CE\#=V_{IL}$, $OE\#=11.4-12V$, $V_{DD}=V_{DD} \text{ Max}$, $WE\#=V_{IL}$
I_{HA9}	Supervoltage Current for A_9		200	μA	
$I_{HOE\#}$	Supervoltage Current for $OE\#$		3	mA	

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TABLE 6: Recommended System Power-up Timings

Symbol	Parameter	Minimum	Units
$T_{PU-READ}^1$	Power-up to Read Operation	100	μs
$T_{PU-WRITE}^1$	Power-up to Write Operation	100	μs

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1. This parameter is measured only for initial qualification and after a design or process change that could affect this parameter.

TABLE 7: Capacitance ($T_A = 25^\circ C$, $f=1 \text{ Mhz}$, other pins open)

Parameter	Description	Test Condition	Maximum
$C_{I/O}^1$	I/O Pin Capacitance	$V_{I/O} = 0V$	12 pF
C_{IN}^1	Input Capacitance	$V_{IN} = 0V$	6 pF

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1. This parameter is measured only for initial qualification and after a design or process change that could affect this parameter.

TABLE 8: Reliability Characteristics

Symbol	Parameter	Minimum Specification	Units	Test Method
N_{END}^1	Endurance	10,000	Cycles	JEDEC Standard A117
T_{DR}^1	Data Retention	100	Years	JEDEC Standard A103
I_{LTH}^1	Latch Up	$100 + I_{DD}$	mA	JEDEC Standard 78

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1. This parameter is measured only for initial qualification and after a design or process change that could affect this parameter.

AC CHARACTERISTICS

TABLE 9: Read Cycle Timing Parameters $V_{DD} = 2.7-3.6V$ ($T_A = 0^\circ C$ to $+70^\circ C$ (Commercial))

Symbol	Parameter	GLS37VF010-70 GLS37VF020-70 GLS37VF040-70		Units
		Min	Max	
T_{RC}	Read Cycle Time	70		ns
T_{CE}	Chip Enable Access Time		70	ns
T_{AA}	Address Access Time		70	ns
T_{OE}	Output Enable Access Time		35	ns
T_{CLZ}^1	CE# Low to Active Output	0		ns
T_{OLZ}^1	OE# Low to Active Output	0		ns
T_{CHZ}^1	CE# High to High-Z Output		25	ns
T_{OHZ}^1	OE# High to High-Z Output		25	ns
T_{OH}^1	Output Hold from Address Change	0		ns

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1. This parameter is measured only for initial qualification and after a design or process change that could affect this parameter.

TABLE 10: Program/Erase Cycle Timing Parameters $V_{DD} = 2.7-3.6V$ ($T_A = 25^\circ C \pm 5^\circ C$)

Symbol	Parameter	Min	Max	Units
T_{BP}	Byte-Program Time		20	μs
T_{CES}	CE# Setup Time	1		μs
T_{CEH}	CE# Hold Time	1		μs
T_{AS}	Address Setup Time	1		μs
T_{AH}	Address Hold Time	1		μs
T_{DS}	Data Setup Time	1		μs
T_{DH}	Data Hold Time	1		μs
T_{PRT}	OE# Rise Time for Program and Erase	50		ns
T_{VPS}	OE# Setup Time for Program and Erase	1		μs
T_{VPH}	OE# Hold Time for Program and Erase	1		μs
T_{PW}	WE# Program Pulse Width	15	25	μs
T_{EW}	WE# Erase Pulse Width	100	200	ms
T_{VR}	OE#/A ₉ Recovery Time for Erase	1		μs
T_{ART}	A ₉ Rise Time to 12V during Erase	50		ns
T_{A9S}	A ₉ Setup Time during Erase	1		μs
T_{A9H}	A ₉ Hold Time during Erase	1		μs

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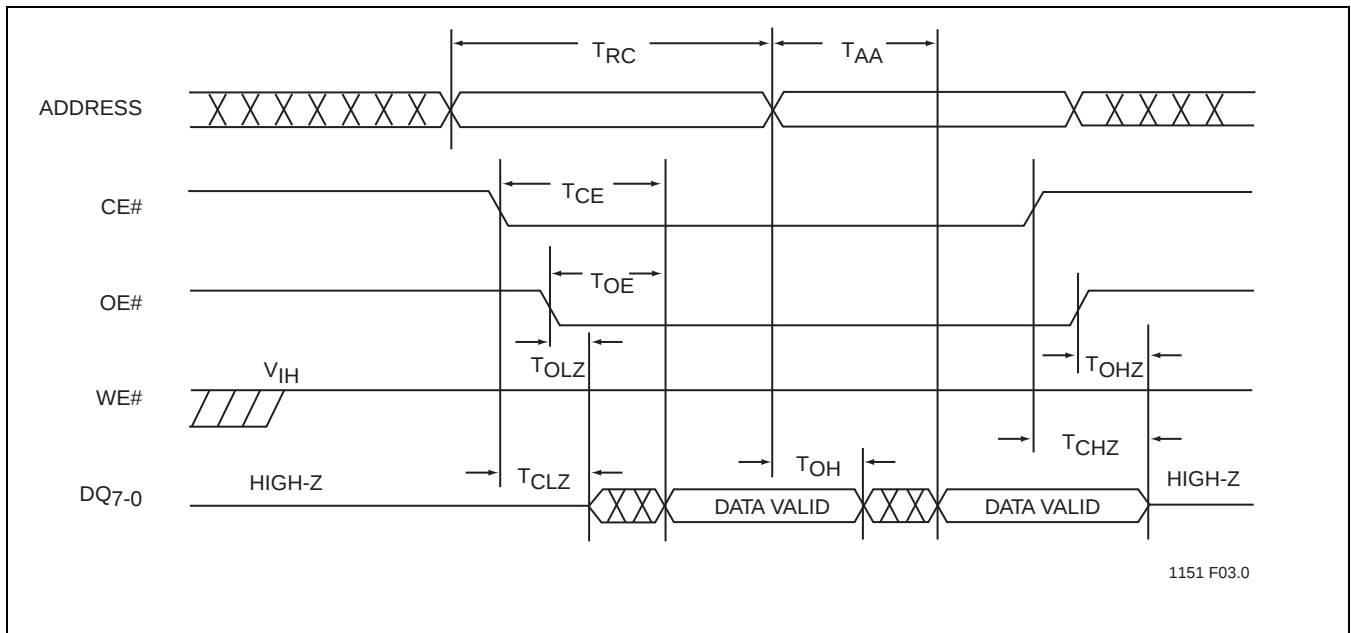


FIGURE 5: Read Cycle Timing Diagram

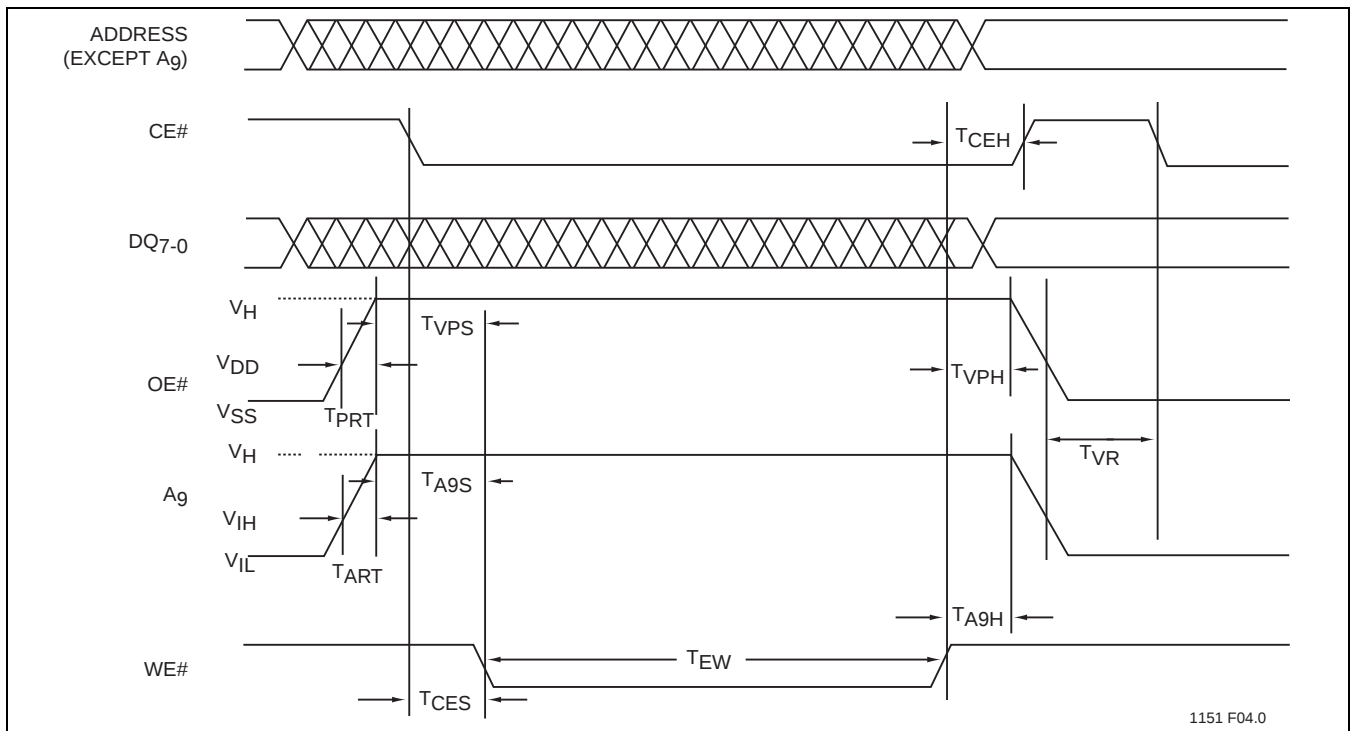


FIGURE 6: Chip-Erase Timing Diagram

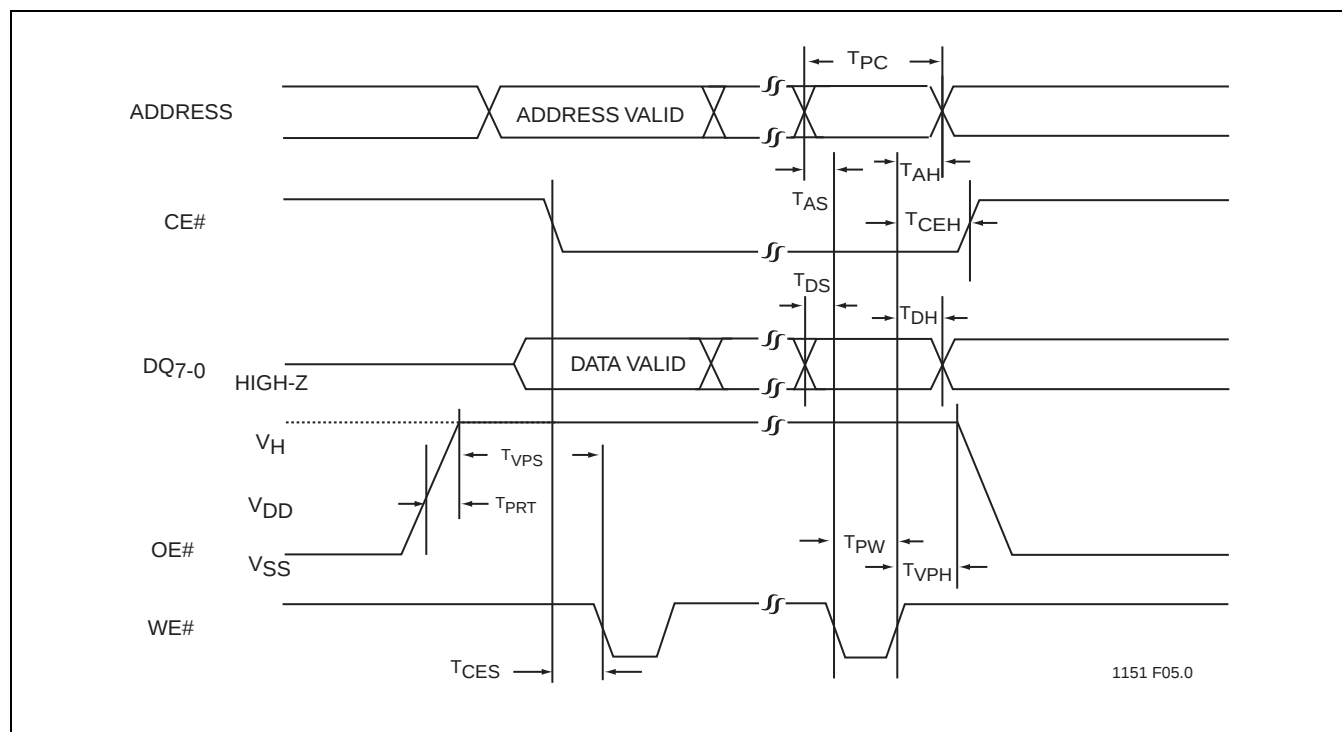
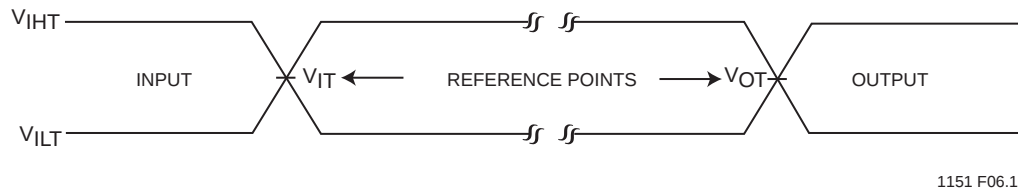


FIGURE 7: Byte-Program Timing Diagram



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AC test inputs are driven at V_{IHT} ($0.9 V_{DD}$) for a logic “1” and V_{ILT} ($0.1 V_{DD}$) for a logic “0”. Measurement reference points for inputs and outputs are V_{IT} ($0.5 V$) and V_{OT} ($0.5 V_{DD}$). Input rise and fall times ($10\% \leftrightarrow 90\%$) are <5 ns.

Note: V_{IT} - V_{INPUT} Test
 V_{OT} - V_{OUTPUT} Test
 V_{IHT} - V_{INPUT} HIGH Test
 V_{ILT} - V_{INPUT} LOW Test

FIGURE 8: AC Input/Output Reference Waveforms

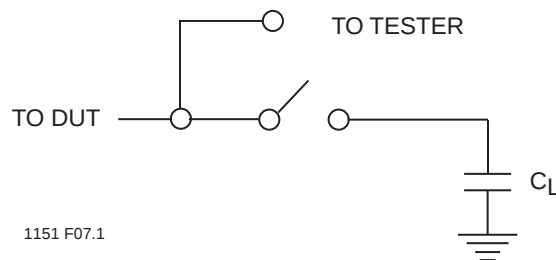


FIGURE 9: A Test Load Example

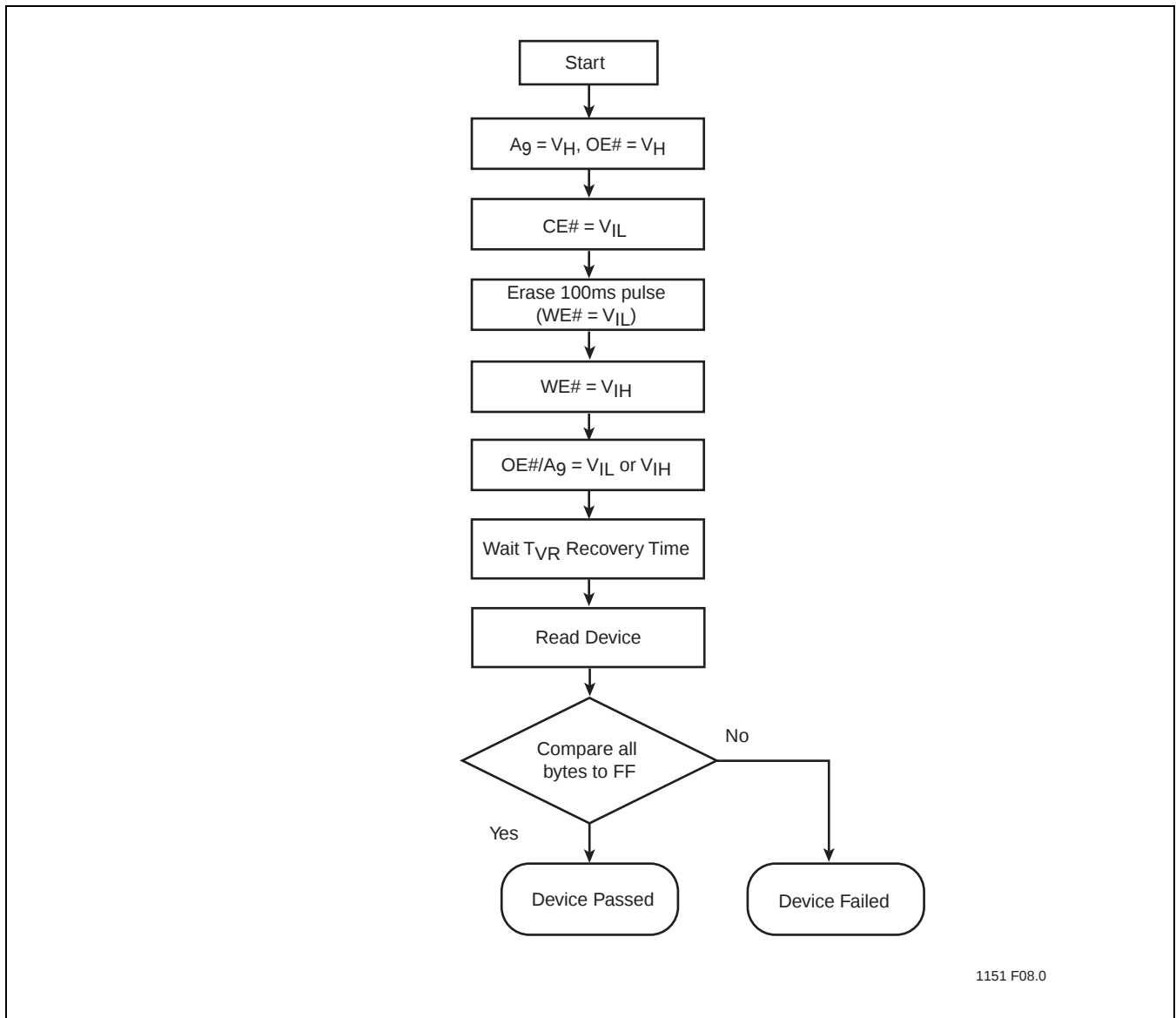
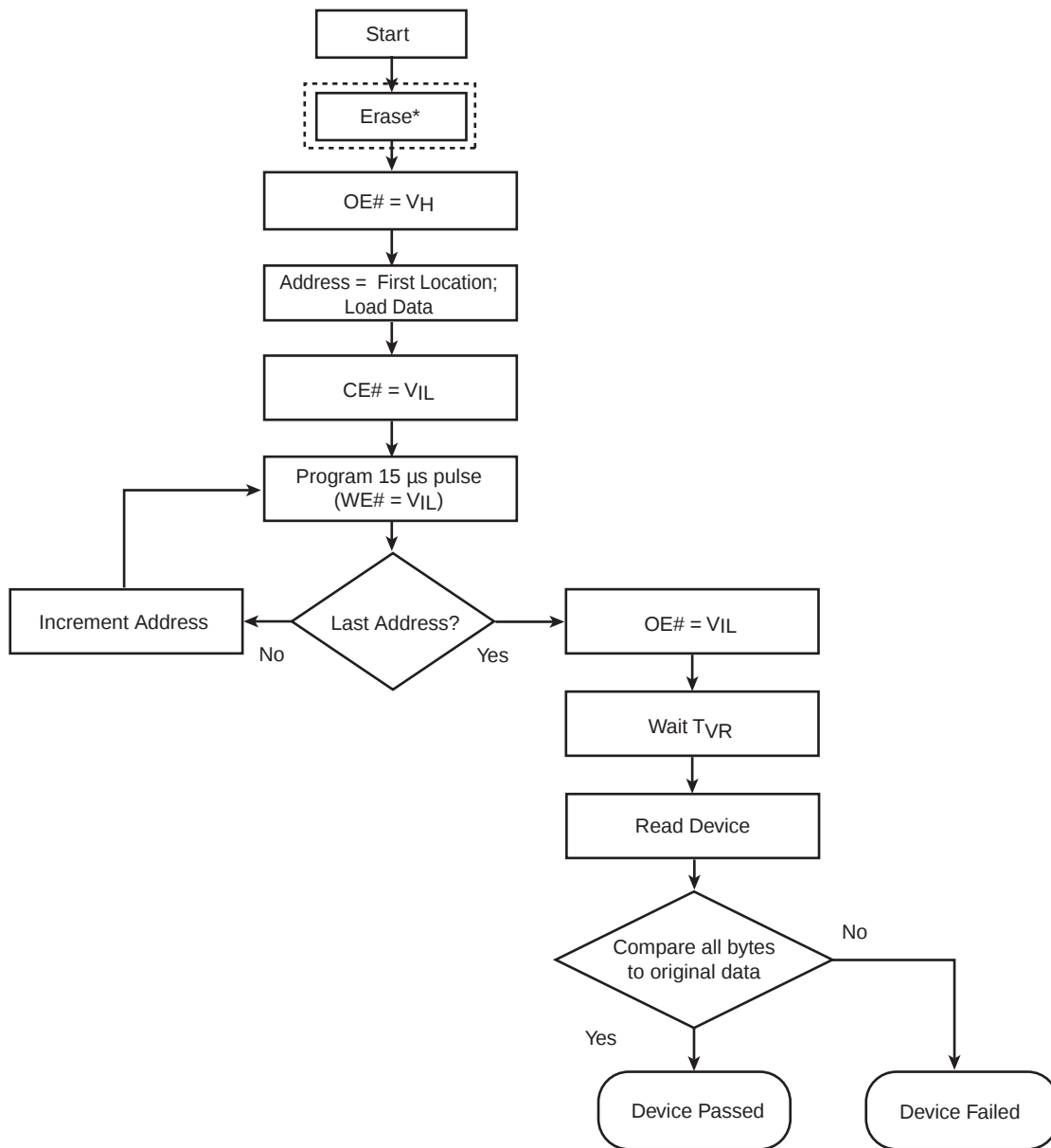


FIGURE 10: Chip-Erase Algorithm



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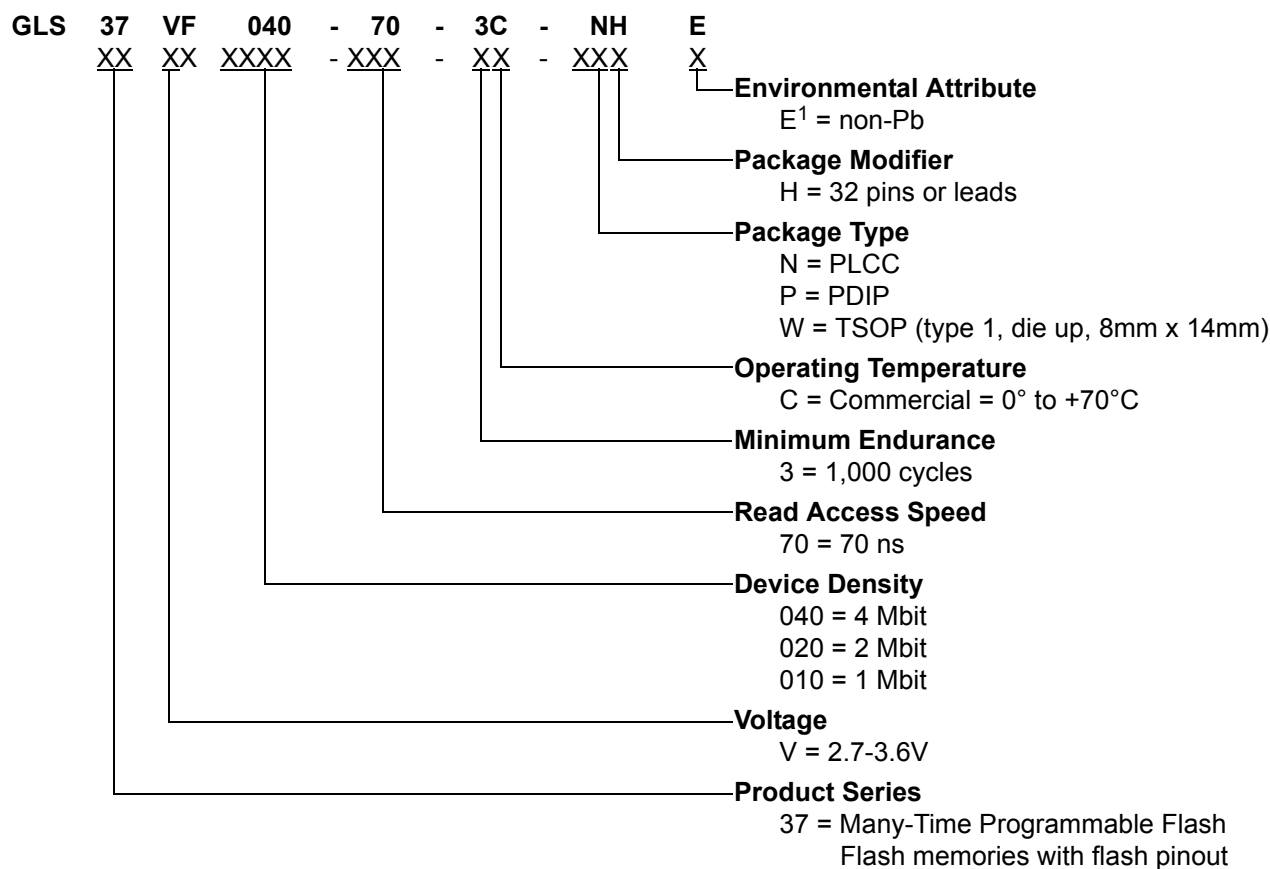


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*See Figure 10

FIGURE 11: Byte-Program Algorithm

PRODUCT ORDERING INFORMATION



1. Environmental suffix "E" denotes non-Pb solder.
 Greenliant non-Pb solder devices are "RoHS Compliant".

Valid combinations for GLS37VF010

GLS37VF010-70-3C-NHE GLS37VF010-70-3C-WHE GLS37VF010-70-3C-PHE

Valid combinations for GLS37VF020

GLS37VF020-70-3C-NHE GLS37VF020-70-3C-WHE GLS37VF020-70-3C-PHE

Valid combinations for GLS37VF040

GLS37VF040-70-3C-NHE GLS37VF040-70-3C-WHE GLS37VF040-70-3C-PHE

Note: Valid combinations are those products in mass production or will be in mass production. Consult your Greenliant sales representative to confirm availability of valid combinations and to determine availability of new combinations.

* Not recommended for new designs.



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PACKAGING DIAGRAMS

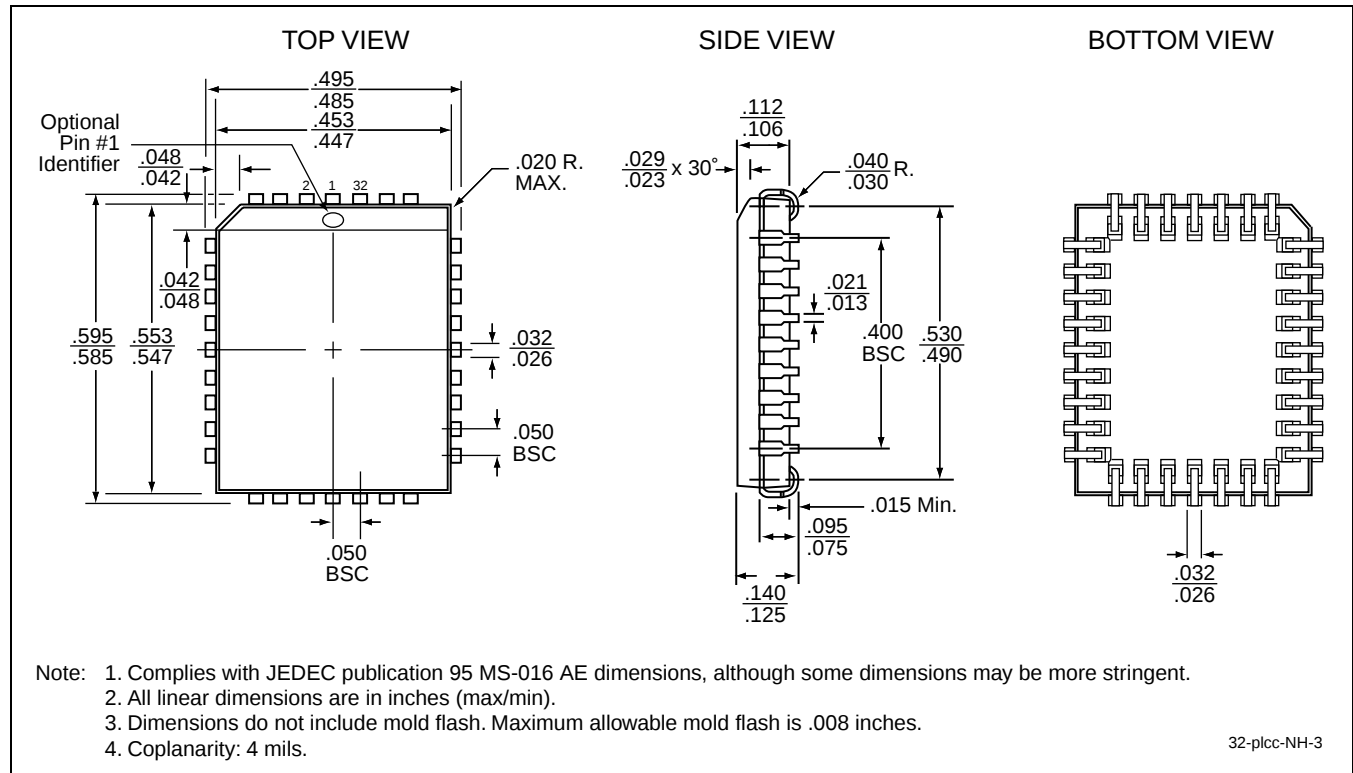


FIGURE 12: 32-lead Plastic Lead Chip Carrier (PLCC)
Greenliant Package Code: NH

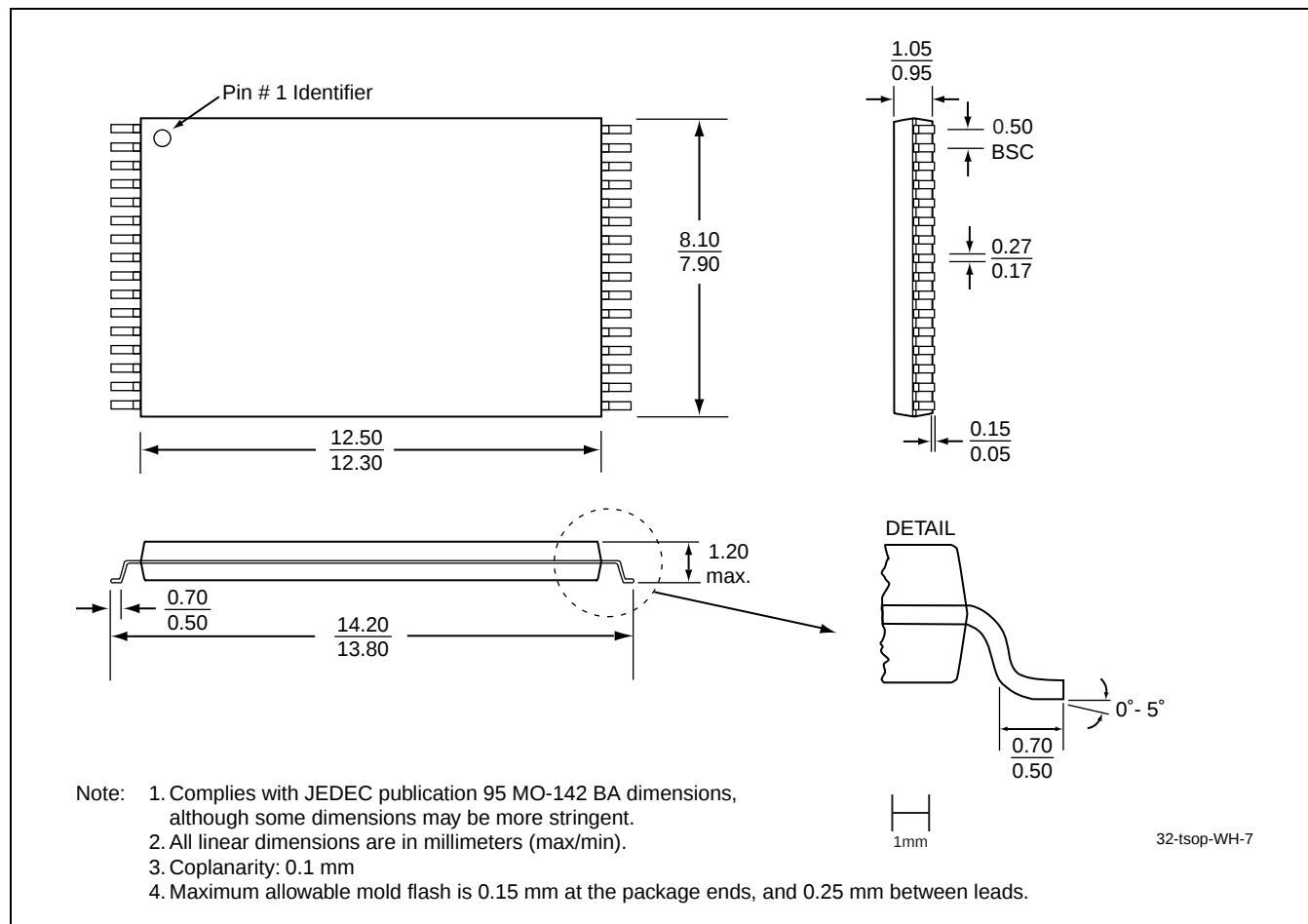


FIGURE 13: 32-lead Thin Small Outline Package (TSOP) 8mm x 14mm
Greenliant Package Code: WH



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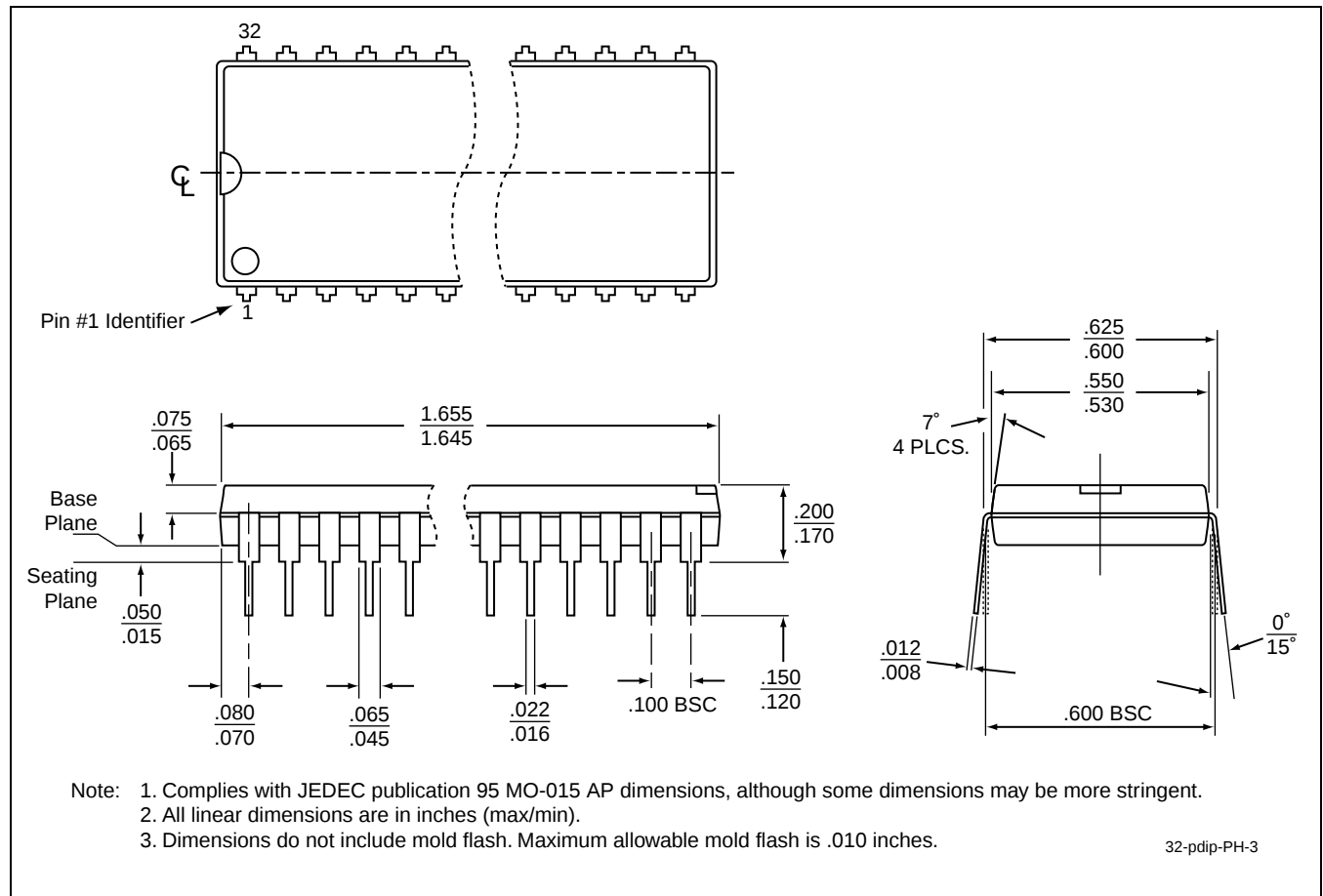


FIGURE 14: 32-pin Plastic Dual In-line Pins (PDIP)
Greenliant Package Code: PH

TABLE 11: Revision History

Number	Description	Date
02	2002 Data Book	Feb 2002
03	- Part number changes - see page 13 for additional information - Clarified the Test Conditions for V_{DD} Read Current parameter in Table 4 on page 5 - Address input = V_{ILT}/V_{IHT} $CE\#=OE\#=V_{ILT}$	Mar 2003
04	2004 Data Book - Added non-Pb MPNs and removed footnote (See page 13)	Nov 2003
05	- Removed 90 ns parts, related footnote, and MPNs (See page 13) - Added 70 ns parts and MPNs for the PH package - Changed Byte-Program time from 10 μs to 15 μs - Updated chip program times - Separated Supervoltage Current for A_9 and $OE\#$ in Table 5 on page 6	May 2004
06	- Added non-Pb 32-PDIP MPNs for 1, 2, and 4 Mbit devices - Clarified the solder temperature profile under "Absolute Maximum Stress Ratings" on page 5	Dec 2004
07	Changed program voltage from 12.6V to 12V globally	Aug 2006
08	- EOLed all valid combinations of SST37VF512, See S71151(03). - Removed 64K x 8 organization and leaded parts	Apr 2007
09	File name correction	Apr 2008
10	Fixed mistake in document status by removing "EOL"	May 2008
11	Transferred from SST to Greenliant	May 2010

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